

N/C

VS-8ETH06S-M3

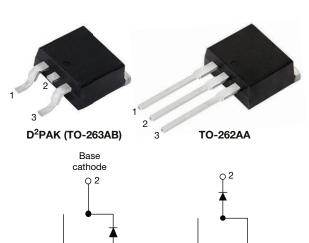
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COMPLIANT

**HALOGEN** 

# Hyperfast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	8 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.3 V				
t <sub>rr</sub> typ.	18 ns				
T <sub>J</sub> max.	175 °C				
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA				
Circuit configuration	Common cathode				

N/C

VS-8ETH06-1-M3

#### **FEATURES**

- · Hyperfast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	$V_{RRM}$		600	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	8				
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	Α			
Peak repetitive forward current	I <sub>FM</sub>		16				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-	.,	
Famoural college	V <sub>F</sub>	I <sub>F</sub> = 8 A	-	2.0	2.4	V	
Forward voltage	٧F	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8		
Povoros loskago ourrent	ı	$V_R = V_R$ rated	-	0.3	50		
Reverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	55	500	μΑ	
Junction capacitance	C <sub>T</sub>	$V_{R} = 600 \text{ V}$	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 1$	00 A/μs, V <sub>R</sub> = 30 V	-	18	22	
Reverse recovery time		$I_F = 8 \text{ A}, dI_F/dt = 1$	00 A/μs, V <sub>R</sub> = 30 V	-	20	25	no
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	-	40	-	
Dools was assemble assemble	,	T <sub>J</sub> = 25 °C		=.	2.4	-	^
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.8	-	Α
Daviere and a constant about	0	T <sub>J</sub> = 25 °C	·n	-	25	-	0
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	nC
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$dI_F/dt = 600 A/\mu s$	-	12	-	Α
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	_	220	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	ı	175	°C
Thermal resistance, junction to case per leg	$R_{thJC}$		-	1.4	2	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	$kgf \cdot cm$ (lbf · in)
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)		8ETI	106S	•
iviai kii ig device		Case style TO-262AA		8ETH	106-1	

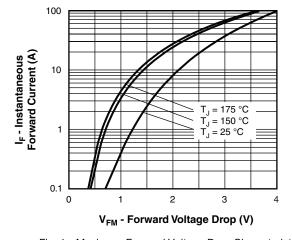


Fig. 1 - Maximum Forward Voltage Drop Characteristics

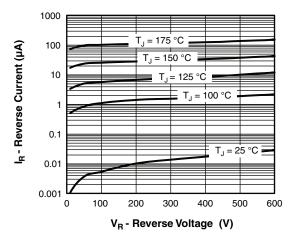


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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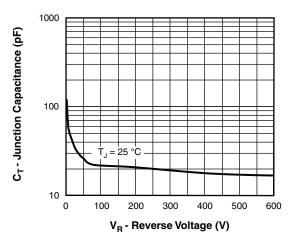


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

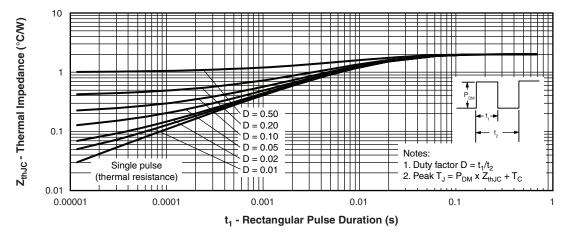


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

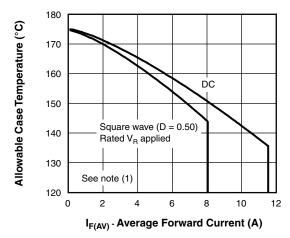


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

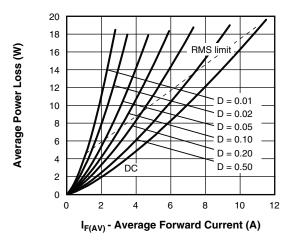


Fig. 6 - Forward Power Loss Characteristics

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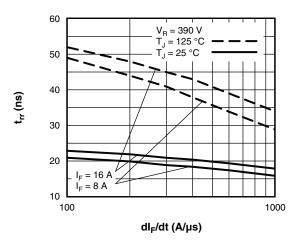


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

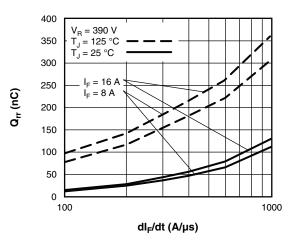
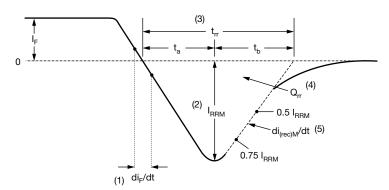


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{r}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions

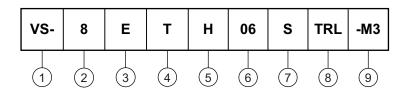


## VS-8ETH06S-M3, VS-8ETH06-1-M3

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (8 A)

3 - E = single diode

- T = TO-220, D<sup>2</sup>PAK (TO-263AB)

5 - H = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - • S =  $D^2$ PAK (TO-263AB)

• -1 = TO-262AA

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK (TO-263AB) package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-8ETH06S-M3	50	Antistatic plastic tubes				
VS-8ETH06STRL-M3	800	13" diameter plastic tape and reel				
VS-8ETH06STRR-M3	800	13" diameter plastic tape and reel				
VS-8ETH06-1-M3	50	Antistatic plastic tubes				

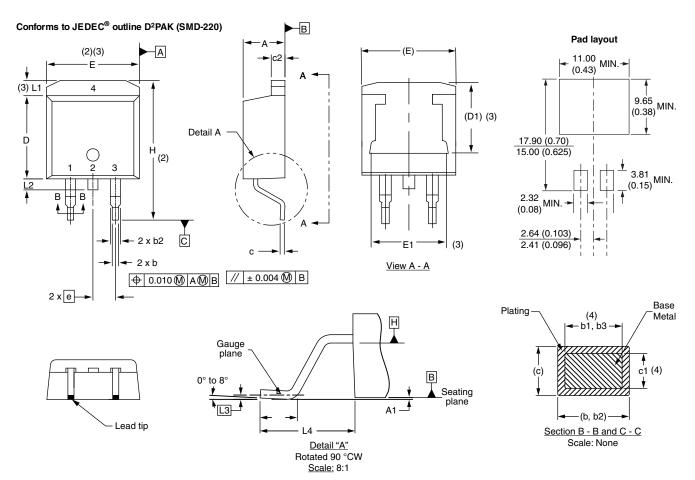
LINKS TO RELATED DOCUMENTS					
Dimensions D <sup>2</sup> PAK (TO-263AB) <u>www.vishay.com/doc?96164</u>					
Differsions –	TO-262AA	www.vishay.com/doc?96165			
Port marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444			
Part marking information –	TO-262AA	www.vishay.com/doc?95443			
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424			



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### D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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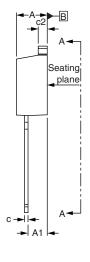


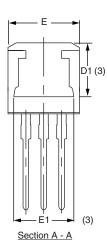
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### **TO-262AA**

#### **DIMENSIONS** in millimeters and inches

# Modified JEDEC® outline TO-262 (2) (3) (3) Ď L2 В (2)





0.010 M AM B

2 x e

#### Lead assignments



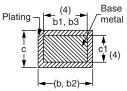
**Diodes** 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode

-3 x b2

**-**3 x b



Section B - B and C - C Scale: None

SYMBOL	MILLIN	METERS	INC	HES	NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100	) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

#### **Notes**

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
  (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- Controlling dimension: inches

  Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

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